

TOSHIBA SM16(G,J)48,USM16(G,J)48,SM16(G,J)48A,USM16(G,J)48A

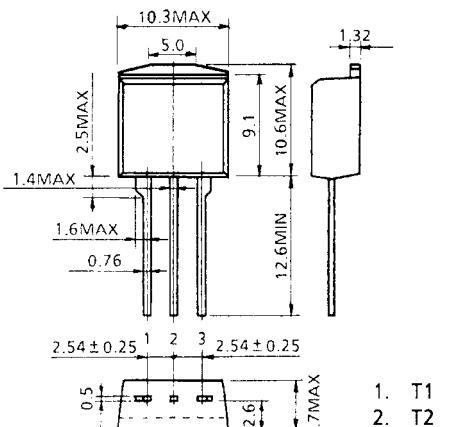
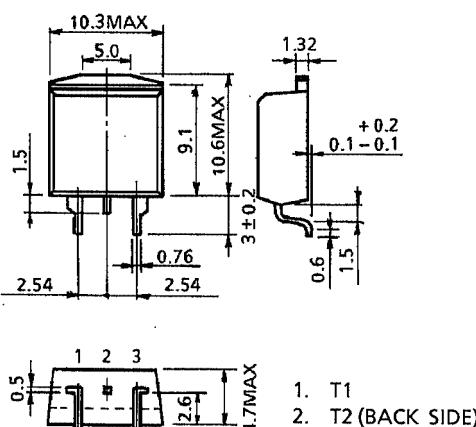
TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

**SM16G48,USM16G48,SM16J48,USM16J48
SM16G48A,USM16G48A,SM16J48A,USM16J48A**

AC POWER CONTROL APPLICATIONS

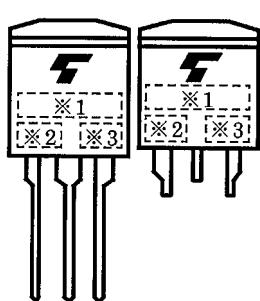
- Repetitive Peak Off-State Voltage : $V_{DRM}=400, 600V$
- R.M.S On-State Current : I_T (RMS)=16A
- Gate Trigger Current : $I_{GT}=30mA$ Max.
: $I_{GT}=20mA$ Max. ("A" Type)

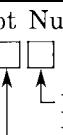
Unit in mm

SM16G48, SM16J48, SM16G48A, SM16J48A	USM16G48, USM16J48, USM16G48A, USM16J48A
 <p>1. T1 2. T2 3. GATE</p>	 <p>1. T1 2. T2 (BACK SIDE) 3. GATE</p>
JEDEC —	JEDEC —
JEITA —	JEITA —
TOSHIBA 13-10J1A	TOSHIBA 13-10J2A

Weight : 1.7g

MARKING



NUMBER	SYMBOL	MARK
*1	SM16G48, SM16G48A, USM16G48, USM16G48A	M16G48
	SM16J48, SM16J48A, USM16J48, USM16J48A	M16J48
*2	SM16G48A, SM16J48A, USM16G48A, USM16J48A	A
*3	Lot Number  Month (Starting from Alphabet A) Year (Last Decimal Digit of the Year of Manufacture)	Example 8A : January 1998 8B : February 1998 8L : December 1998

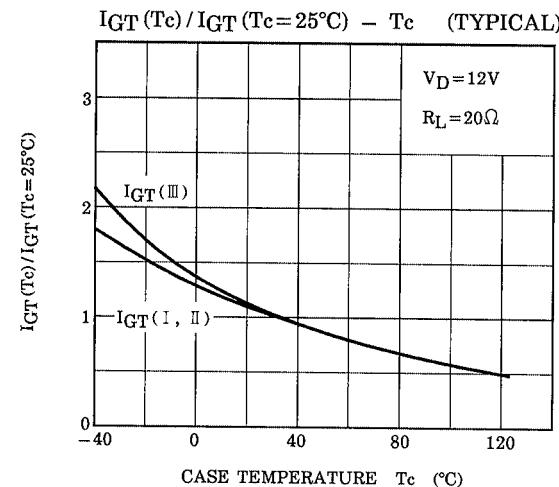
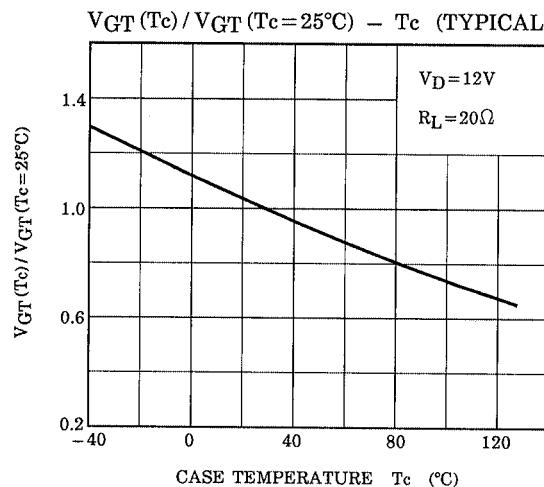
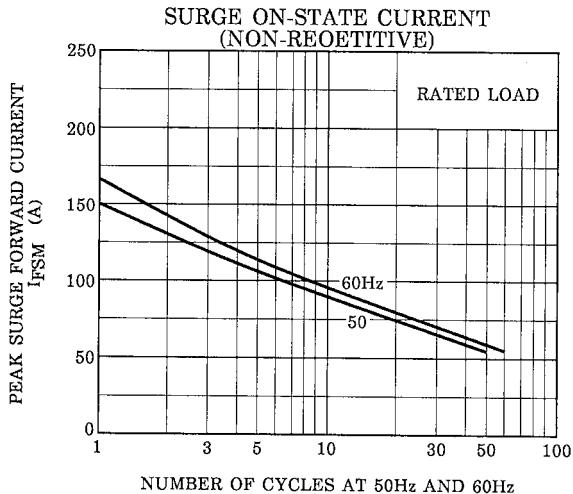
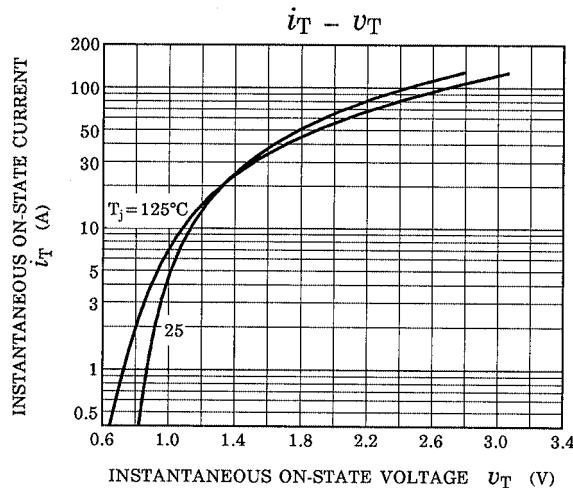
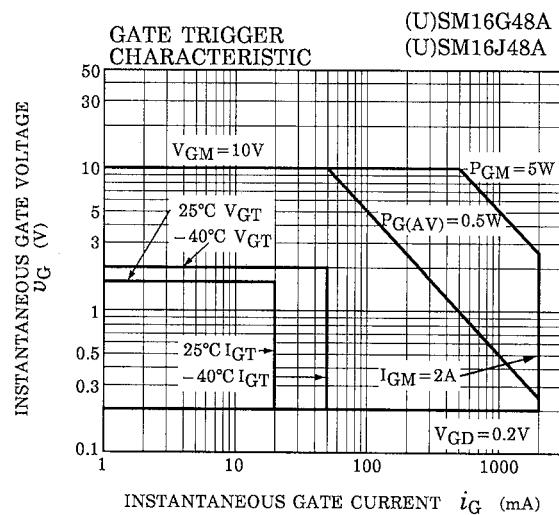
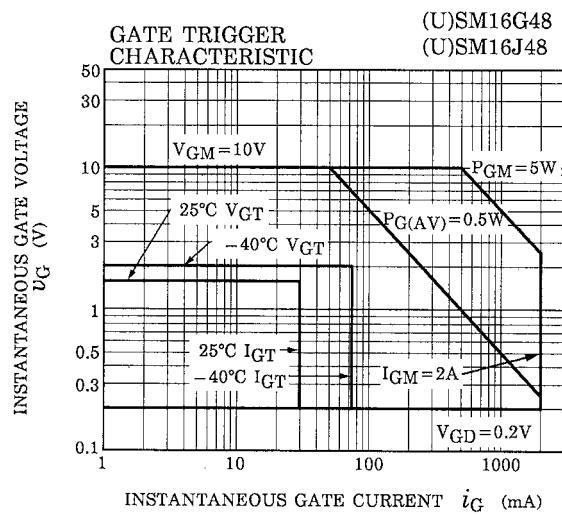
MAXIMUM RATINGS (Ta=25°C)

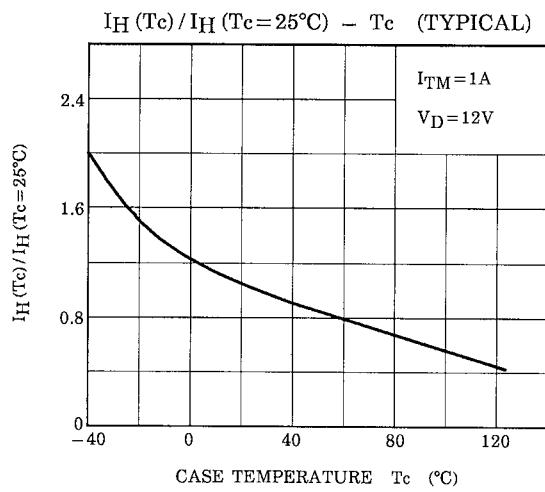
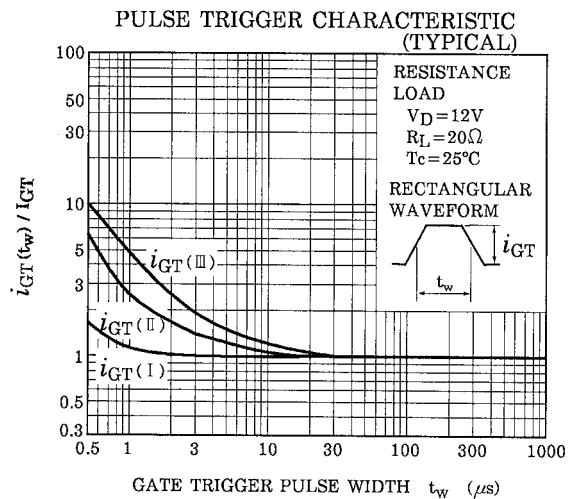
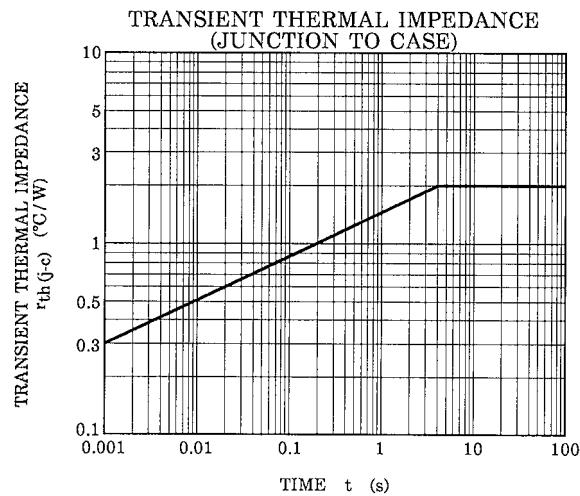
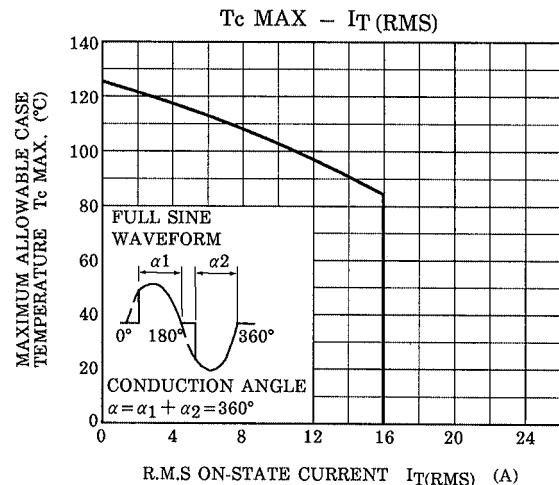
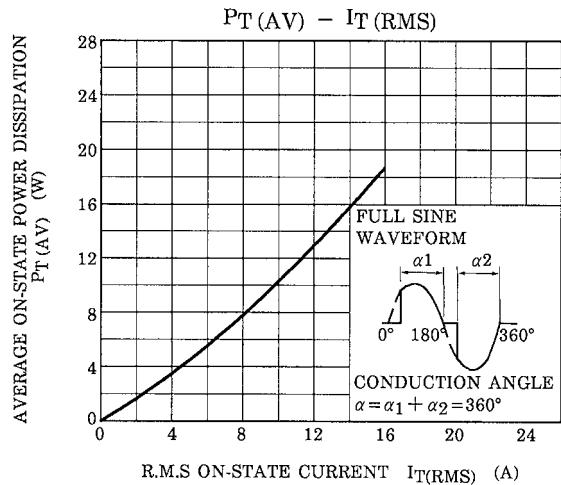
CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage	(U)SM12G48 (U)SM12G48A	V _{DRM}	400	V
	(U)SM12J48 (U)SM12J48A		600	
R.M.S On-State Current		I _T (RMS)	16	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		I _{TSM}	150 (50Hz)	A
			165 (60Hz)	
I ² _t Limit Value		I ² _t	112.5	A ² s
Critical Rate of Rise of On-State Current (Note 1)		di /dt	50	A / μs
Peak Gate Power Dissipation		P _{GM}	5	W
Average Gate Power Dissipation		P _G (AV)	0.5	W
Peak Forward Gate Voltage		V _{GM}	10	V
Peak Forward Gate Current		I _{GM}	2	A
Junction Temperature		T _j	-40~125	°C
Storage Temperature Range		T _{stg}	-40~125	°C

Note 1 : V_{DRM}=0.5×Rated
I_{TM}≤25A
t_{gw}≥10μs
t_{gr}≤250ns
i_{gp}=I_{GT}×2.0

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Repetitive Peak Off-State Current		I _{DRM}	V _{DRM} =Rated		—	—	20	μA
Gate Trigger Voltage	I	V _{GT}	V _D =12V R _L =20Ω	T2 (+), Gate (+)	—	—	1.5	V
	II			T2 (+), Gate (-)	—	—	1.5	
	III			T2 (-), Gate (-)	—	—	1.5	
	IV			T2 (-), Gate (+)	—	—	—	
Gate Trigger Current	I	I _{GT}	V _D =12V R _L =20Ω	T2 (+), Gate (+)	—	—	30	mA
	II			T2 (+), Gate (-)	—	—	30	
	III			T2 (-), Gate (-)	—	—	30	
	IV			T2 (-), Gate (+)	—	50	—	
	I			T2 (+), Gate (+)	—	—	20	
	II			T2 (+), Gate (-)	—	—	20	
	III			T2 (-), Gate (-)	—	—	20	
	IV			T2 (-), Gate (+)	—	—	—	
Peak On-State Voltage		V _{TM}	I _{TM} =17A		—	—	1.5	—
Gate Non-Trigger Voltage		V _{GD}	V _D =Rated, T _c =125°C		0.2	—	—	V
Holding Current		I _H	V _D =12V, I _{TM} =1A		—	—	50	mA
Thermal Resistance		R _{th} (j-c)	Junction to Case, AC		—	—	2.0	°C / W
Critical Rate of Rise of Off-State Voltage	(U)SM16G48 (U)SM16J48	dv / dt	V _{DRM} =Rated, T _j =125°C Exponential Rise		—	300	—	V / μs
	(U)SM16G48A (U)SM16J48A				—	200	—	
Critical Rate of Rise of Off-State Voltage at Commutation	(U)SM16G48 (U)SM16J48	(dv / dt) c	V _{DRM} =400V, T _j =125°C (di / dt) c=-8.7A / ms		10	—	—	V / μs
	(U)SM16G48A (U)SM16J48A				4	—	—	





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